



**General Description**

The ZM110P06D combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

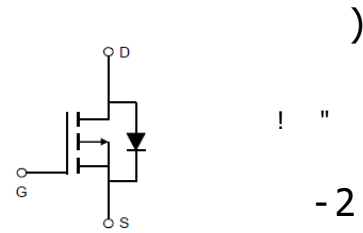
**Features**

- Trench technology
- $R_{DS(ON)}$  to minimize conductive loss

**Application**

nd Synchronous Rectifier

**Product Summary**



**Ordering Information:**

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	) )
	REEL TAPE
! "	2500

**Absolute Maximum Ratings  $T_c = 25$**

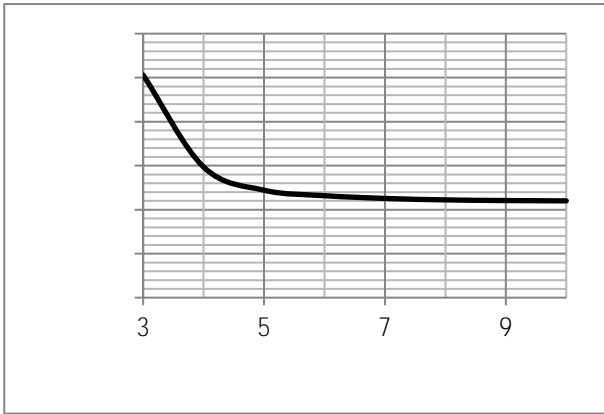
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ TC=25$	-49	A
	$I_D @ TC=75$	-37	A
	$I_D @ TC=100$	-31	A
Pulsed Drain Current	$I_{DM}$	-147	A
Total Power Dissipation	$P_D @ TC=25$	55	W
Total Power Dissipation	$P_D @ TA=25$	3.5	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy @ $L=0.1mH$	$E_{AS}$	820	mJ







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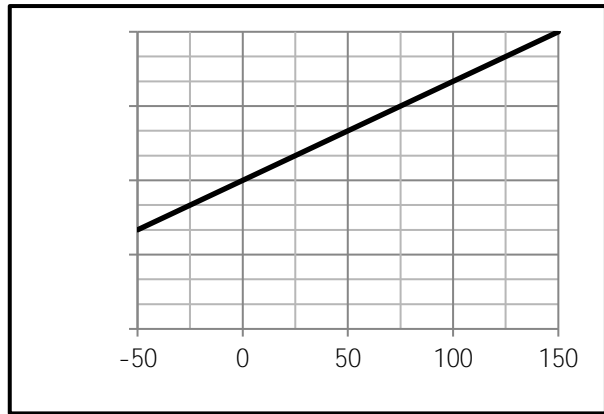


Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

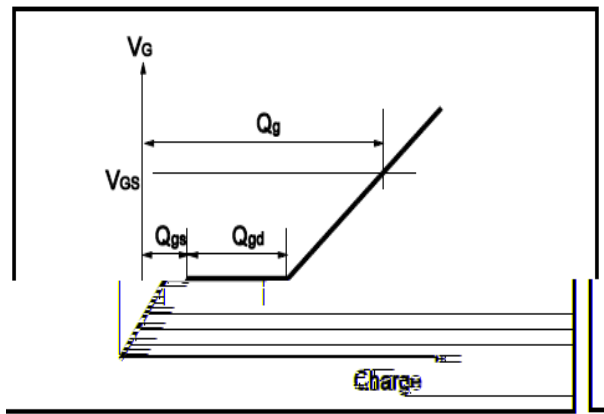
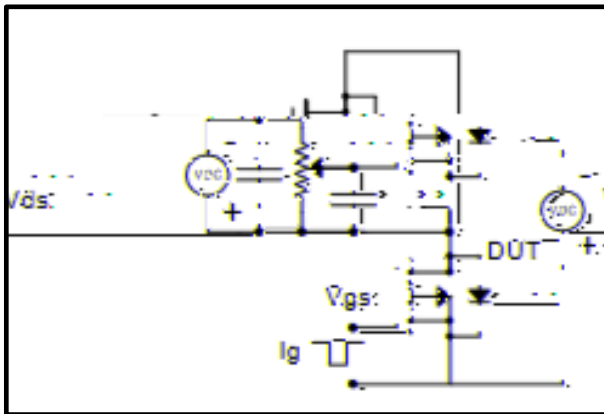
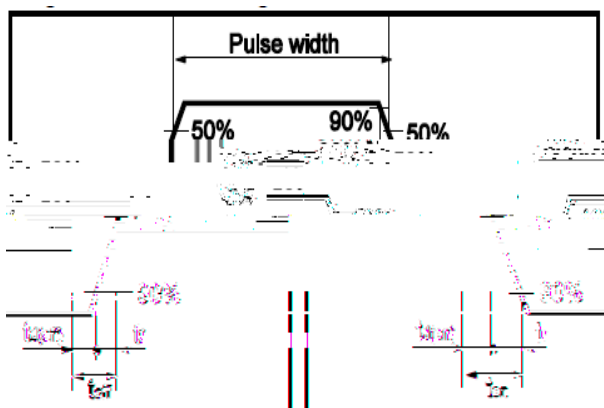
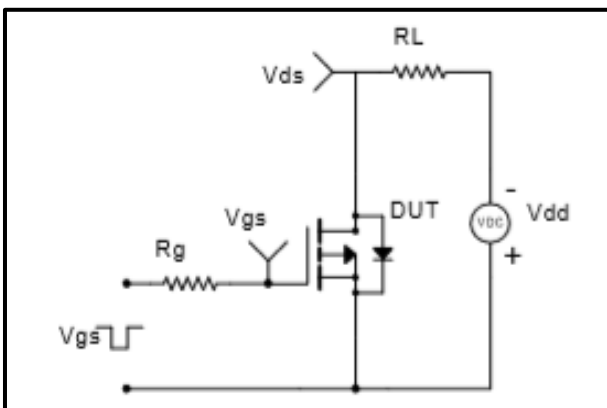


Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform





Dimensions (TO-252)

Unit mm

SYMBOL	mi n	max	SYMBOL	mi n	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

